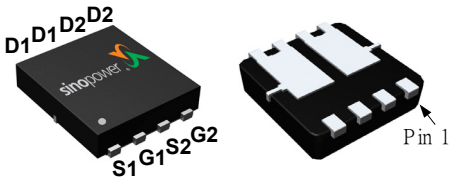
Dual Enhancement Mode MOSFET (N-and P-Channel)

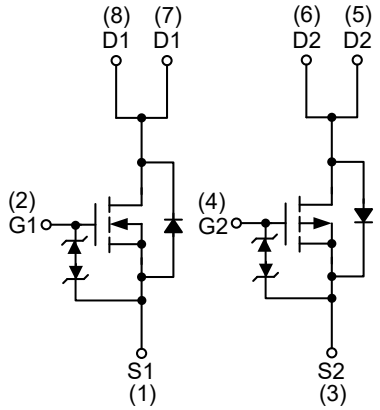
Features

- N Channel : 150V/7.3A,
  $R_{DS(ON)}$=211mΩ(max.)@V_{GS}=10V
  $R_{DS(ON)}$=235mΩ(max.)@V_{GS}=4.5V
- P Channel : -150V/-7.3A,
  $R_{DS(ON)}$=283mΩ(max.)@V_{GS}=-10V
  $R_{DS(ON)}$=319mΩ(max.)@V_{GS}=-4.5V
- 100% UIS + R_g Tested
- ESD Protection
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

Pin Description



DFN5x6C-8_EP2



N-Channel MOSFET P-Channel MOSFET

Applications

- DC Motor Control.

Ordering and Marking Information

SM1F05CS □□□-□□ □ Assembly Material Handling Code Temperature Range Package Code	Package Code KP : DFN5x6C-8_EP2 Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape & Reel Assembly Material G : Halogen and Lead Free Device
SM1F05CS KP : 1F05CS XXXXX	XXXXX - Lot Code

Note : SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

SINOPOWER reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter		N Channel	P Channel	Unit
Common Ratings					
V_{DSS}	Drain-Source Voltage		150	-150	V
V_{GSS}	Gate-Source Voltage		±20	±20	
T_J	Maximum Junction Temperature		150		°C
T_{STG}	Storage Temperature Range		-55 to 150		
I_S	Diode Continuous Forward Current	T_C=25°C	3.6	-3.6	A
I_D	Continuous Drain Current	T_C=25°C	7.3	-7.3	A
		T_C=100°C	4.6	-4.6	
I_{DM} [a]	Pulse Drain Current Tested	T_C=25°C	22	-22	A
P_D	Maximum Power Dissipation	T_C=25°C	25	31	W
		T_C=100°C	10	12	
$R_{\theta JC}$	Thermal Resistance-Junction to Case		5	4	°C/W
I_D	Continuous Drain Current	T_A=25°C	1.9	-1.7	A
		T_A=70°C	1.5	-1.3	
P_D	Maximum Power Dissipation	T_A=25°C	1.7	1.7	W
		T_A=70°C	1.1	1.1	
$R_{\theta JA}$ [c]	Thermal Resistance-Junction to Ambient		75		°C/W
I_{AS} [b]	Avalanche Current, Single pulse	L=0.5mH	3	-13	A
E_{AS} [b]	Avalanche Energy, Single pulse	L=0.5mH	2.25	42.3	mJ

Note a : Pulse width limited by maximum junction temperature.
Note b : UIS tested and pulse width limited by maximum junction temperature (initial temperature T_j=25°C).
Note c : Surface mounted on 1in^2 pad area.

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N Channel Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	N Channel Min.	N Channel Typ.	N Channel Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250μA	150	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=120V, V_{GS}=0V	-	-	1	μA
		T_J=85°C	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	1.5	2	3	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±10	μA
$R_{DS(ON)}$ [d]	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=3.2A	-	176	211	mΩ
		V_{GS}=4.5V, I_{DS}=2A	-	181	235	
Diode Characteristics						
V_{SD} [d]	Diode Forward Voltage	I_{SD}=1.6A, V_{GS}=0V	-	0.8	1.1	V
t_{rr}	Reverse Recovery Time	I_{SD}=3.2A, dI_{SD}/dt=100A/μs	-	45	-	ns
Q_{rr}	Reverse Recovery Charge		-	74	-	nC
Dynamic Characteristics [e]						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V,f=1MHz	-	3	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=75V, Frequency=1.0MHz	-	700	910	pF
C_{oss}	Output Capacitance		-	32	-	
C_{rss}	Reverse Transfer Capacitance		-	14	-	
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=30V, R_L=30Ω, I_{DS}=1A, V_{GEN}=10V, R_G=6Ω	-	10	18	ns
t_r	Turn-on Rise Time		-	6	11	
$t_{d(OFF)}$	Turn-off Delay Time		-	23	41	
t_f	Turn-off Fall Time		-	6	11	
Gate Charge Characteristics [e]						
Q_g	Total Gate Charge	V_{DS}=75V, V_{GS}=10V, I_{DS}=3.2A	-	12	17	nC
Q_g	Total Gate Charge	V_{DS}=75V, V_{GS}=4.5V, I_{DS}=3.2A	-	5.7	8	
Q_{gs}	Gate-Source Charge		-	2.2	-	
Q_{gd}	Gate-Drain Charge		-	2.1	-	

Note d：Pulse test ; pulse width≤300μs, duty cycle≤2%.
Note e：Guaranteed by design, not subject to production testing.

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P Channel Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	P Channel			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=-250μA	-150	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-120V, V_{GS}=0V	-	-	-1	μA
		T_J=85°C	-	-	-30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	-1.5	-2	-3	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±10	μA
$R_{DS(ON)}$ [d]	Drain-Source On-state Resistance	V_{GS}=-10V, I_{DS}=-3A	-	236	283	mΩ
		V_{GS}=-4.5V, I_{DS}=-2A	-	245	319	
Diode Characteristics						
V_{SD} [d]	Diode Forward Voltage	I_{SD}=-1.5A, V_{GS}=0V	-	-0.8	-1.1	V
t_{rr}	Reverse Recovery Time	I_{SD}=-3A, dI_{SD}/dt=100A/μs	-	42	-	ns
Q_{rr}	Reverse Recovery Charge		-	88	-	nC
Dynamic Characteristics [e]						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V,f=1MHz	-	11	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-75V, Frequency=1.0MHz	-	1250	1630	pF
C_{oss}	Output Capacitance		-	53	-	
C_{rss}	Reverse Transfer Capacitance		-	36	-	
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=-30V, R_L=-30Ω, I_{DS}=-1A, V_{GEN}=-10V, R_G=6Ω	-	10	18	ns
t_r	Turn-on Rise Time		-	10	18	
$t_{d(OFF)}$	Turn-off Delay Time		-	91	164	
t_f	Turn-off Fall Time		-	116	209	
Gate Charge Characteristics [e]						
Q_g	Total Gate Charge	V_{DS}=-75V, V_{GS}=-10V, I_{DS}=-3A	-	30	42	nC
Q_g	Total Gate Charge	V_{DS}=-75V, V_{GS}=-4.5V, I_{DS}=-3A	-	15	21	
Q_{gs}	Gate-Source Charge		-	3.7	-	
Q_{gd}	Gate-Drain Charge		-	7.4	-	

Note d：Pulse test ; pulse width≤300μs, duty cycle≤2%.
Note e：Guaranteed by design, not subject to production testing.

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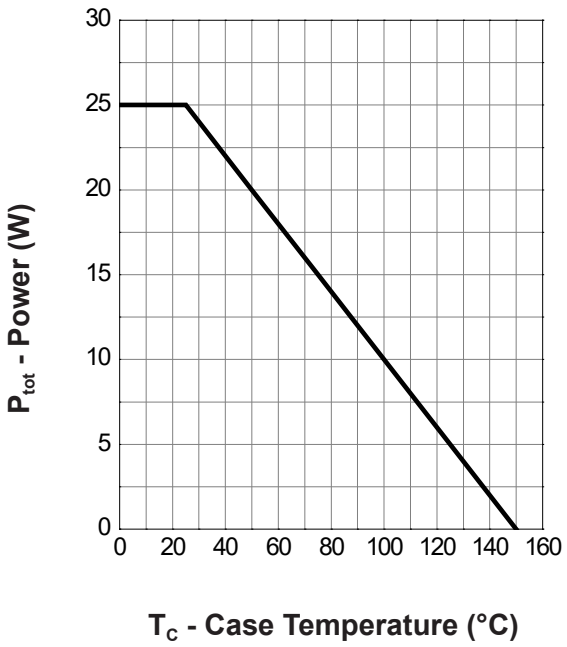
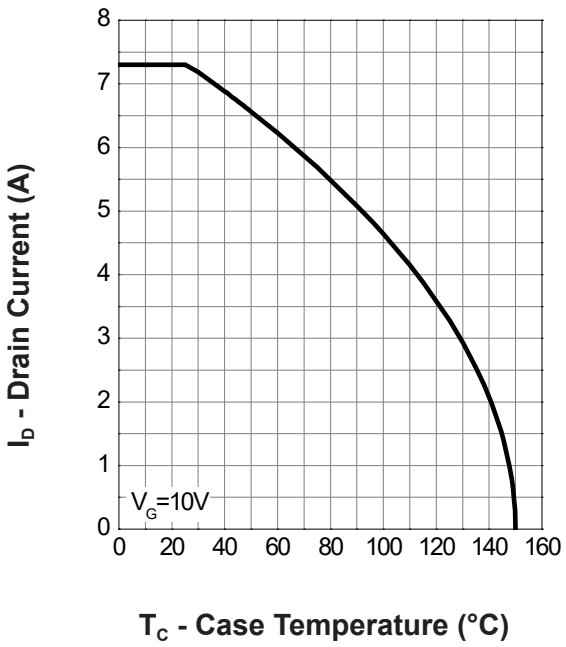
N Channel Typical Operating Characteristics

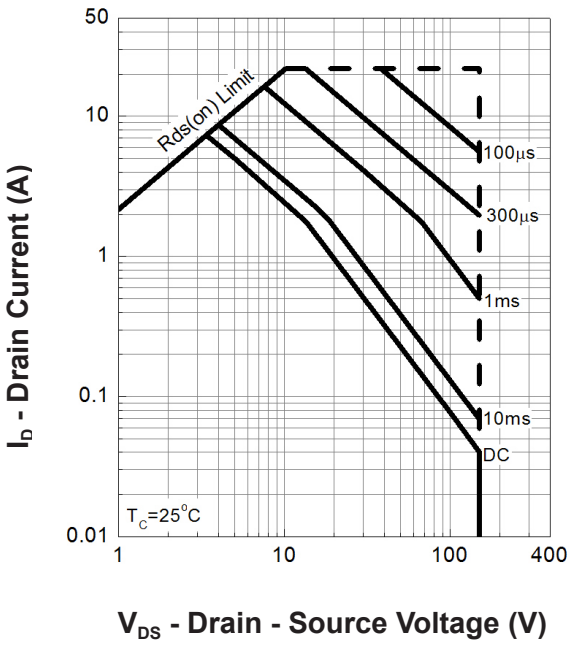
Power Dissipation



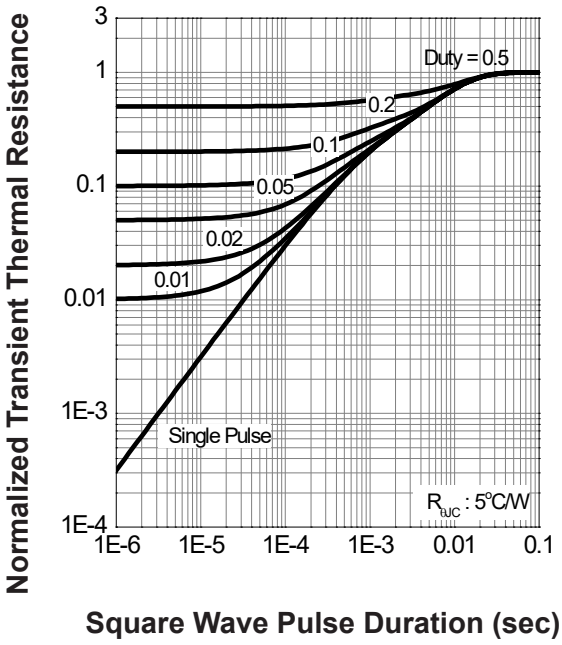
Drain Current



Safe Operation Area

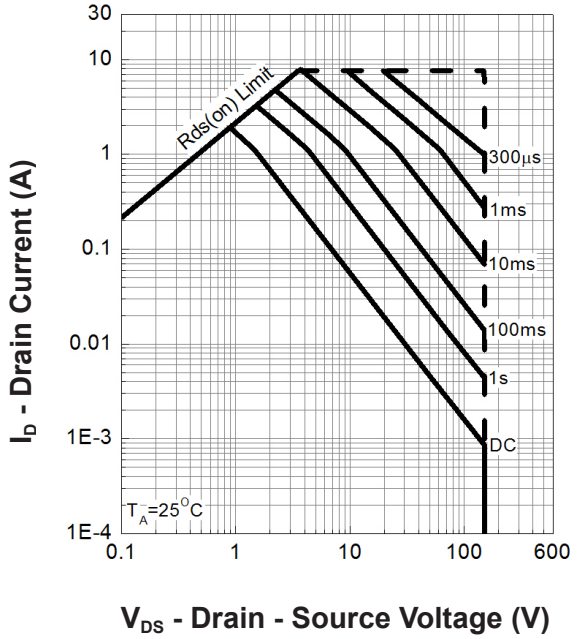


Thermal Transient Impedance

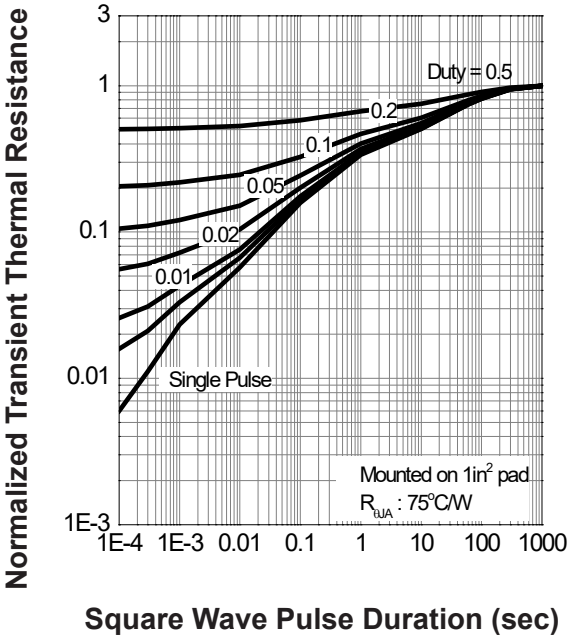


N Channel Typical Operating Characteristics(Cont.)

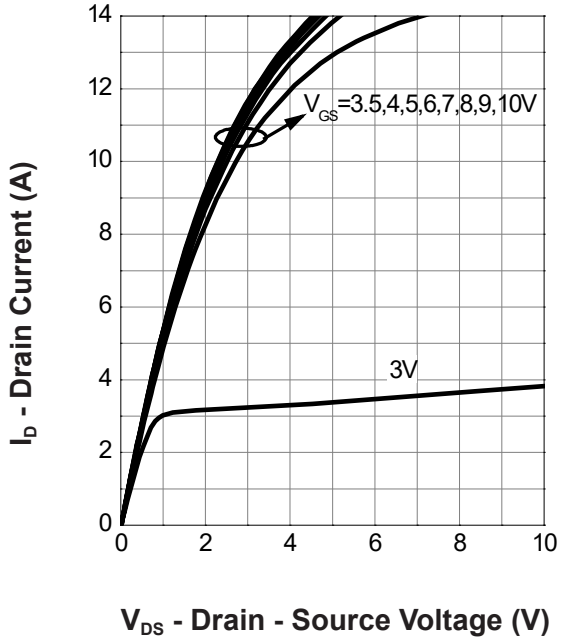
Safe Operation Area



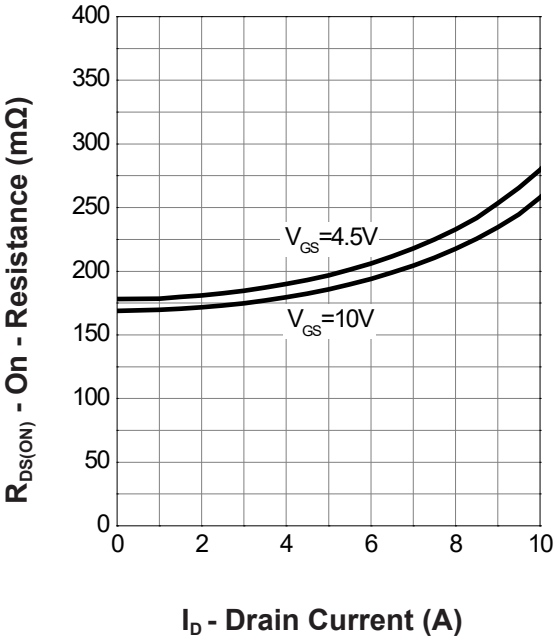
Thermal Transient Impedance



Output Characteristics



Drain-Source On Resistance



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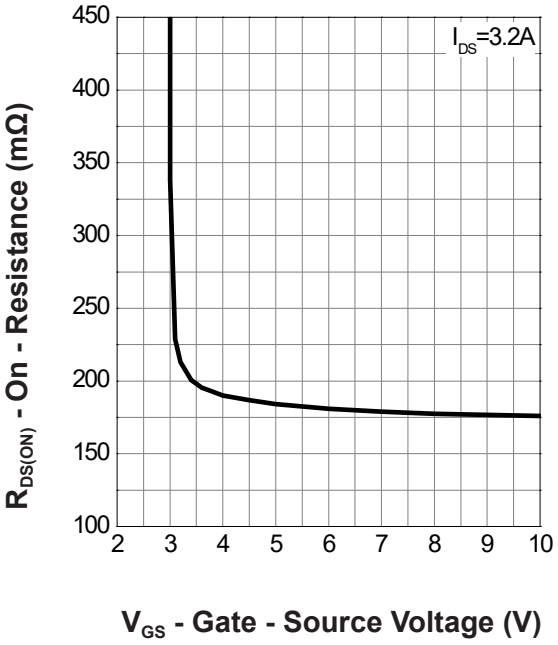
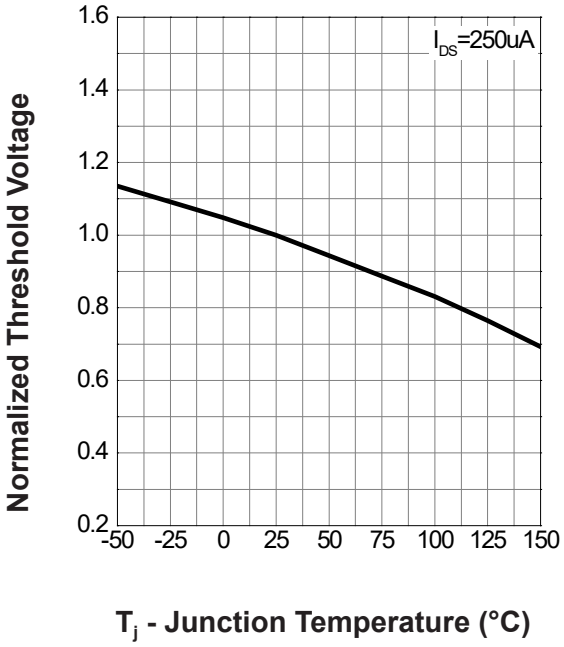
N Channel Typical Operating Characteristics(Cont.)

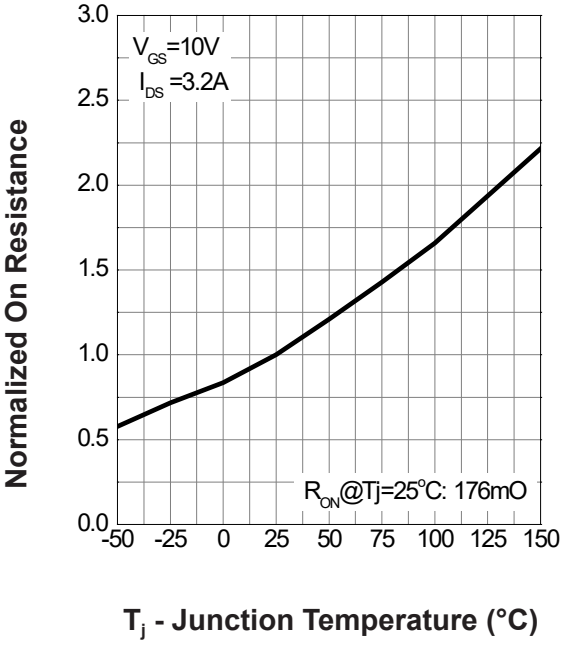
Gate-Source On Resistance



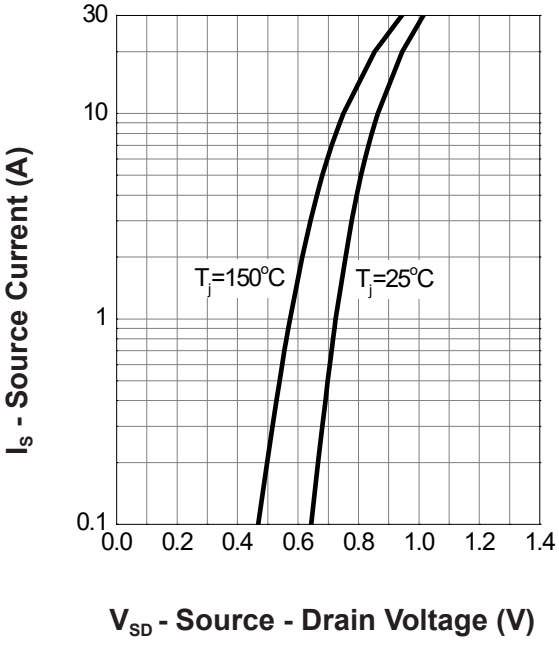
Gate Threshold Voltage



Drain-Source On Resistance



Source-Drain Diode Forward



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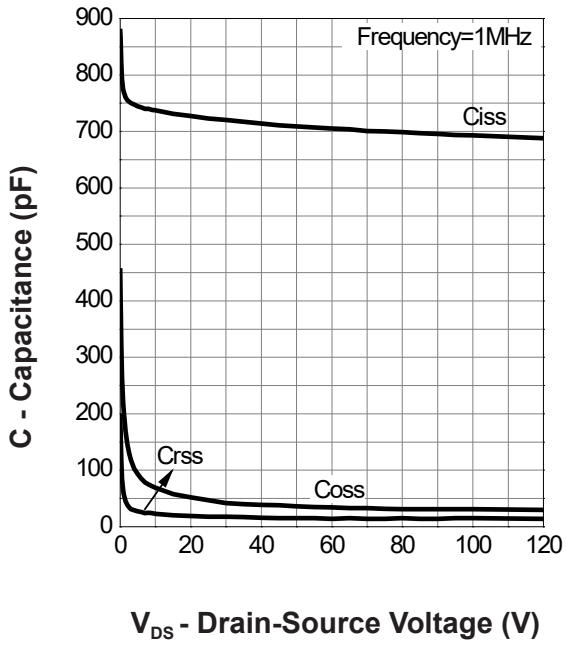
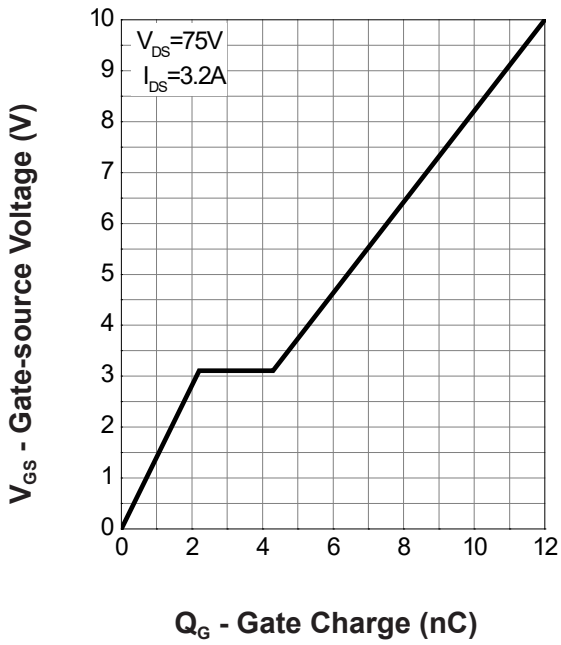
N Channel Typical Operating Characteristics(Cont.)

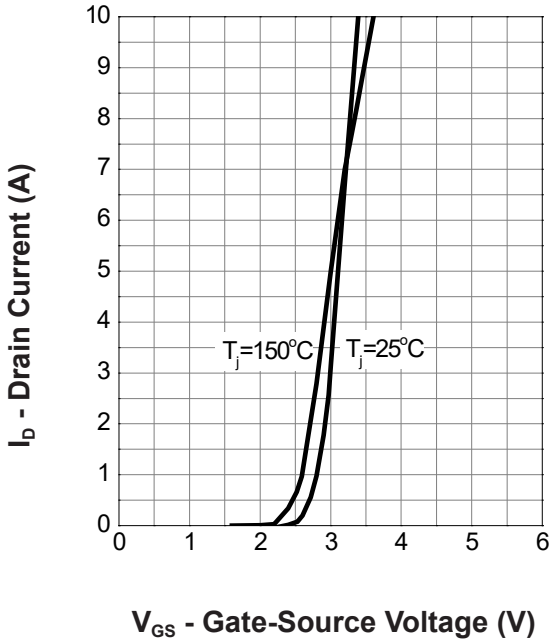
Capacitance



Gate Charge

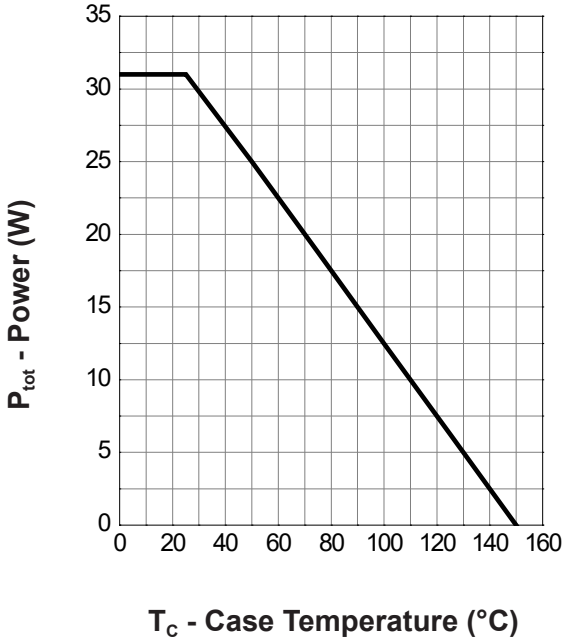


Transfer Characteristics

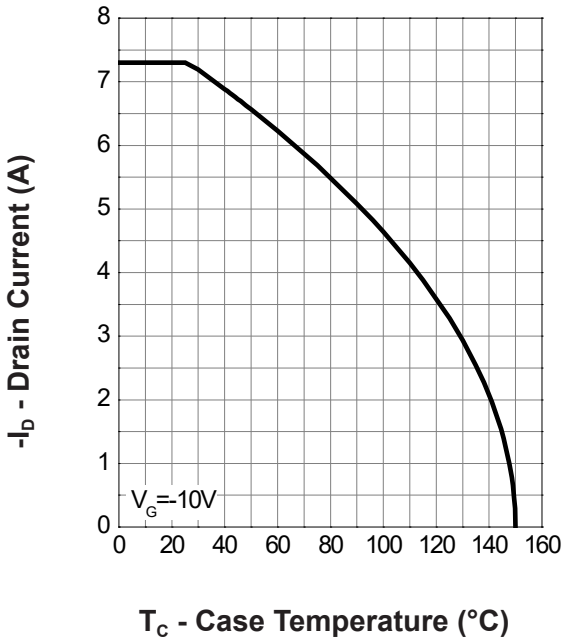


P Channel Typical Operating Characteristics

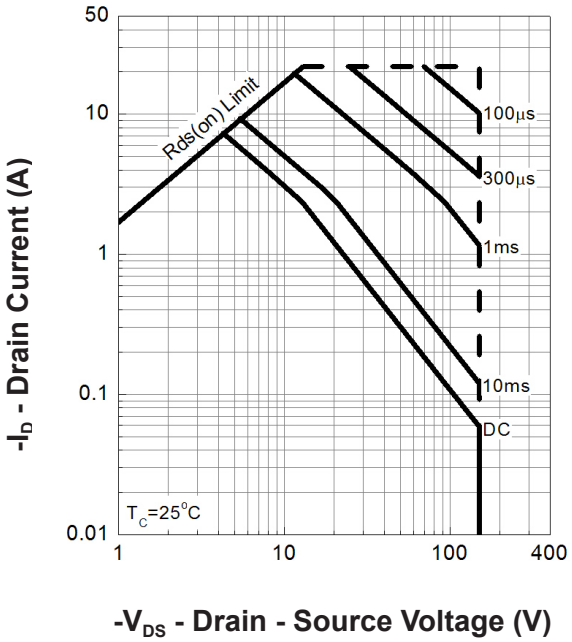
Power Dissipation



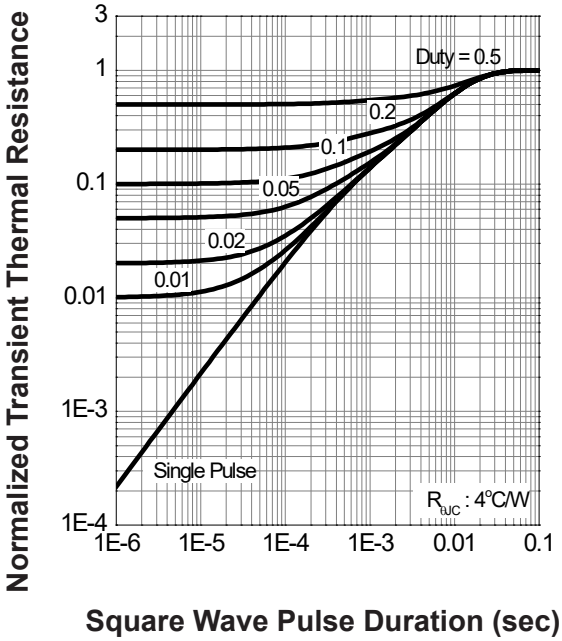
Drain Current



Safe Operation Area

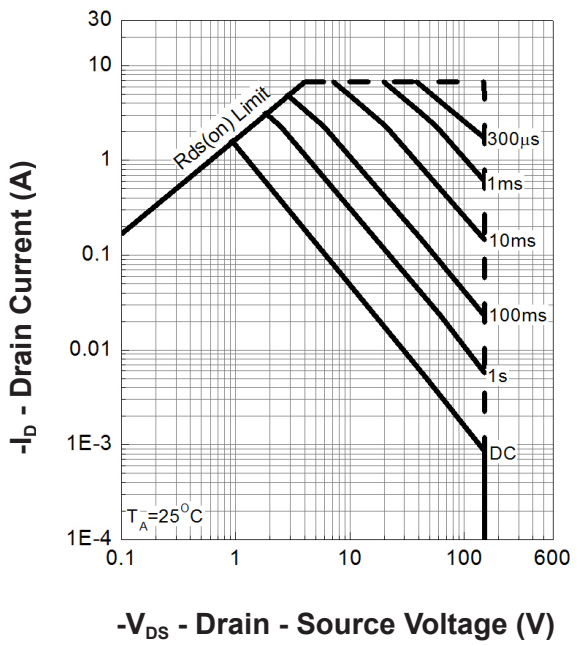


Thermal Transient Impedance

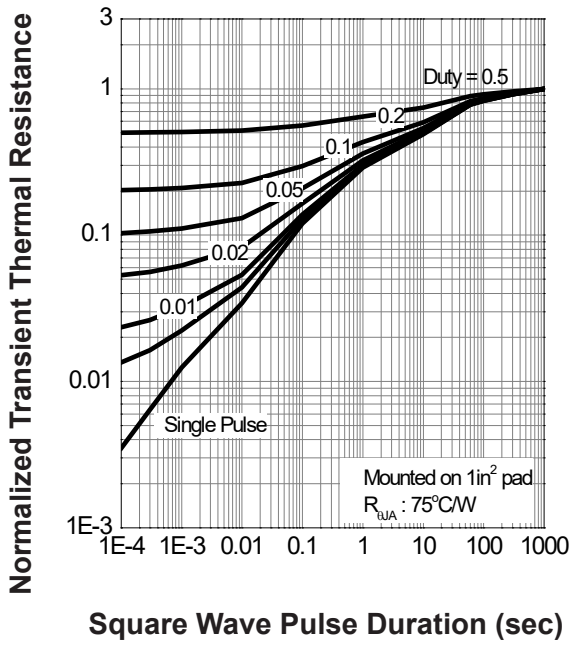


P Channel Typical Operating Characteristics(Cont.)

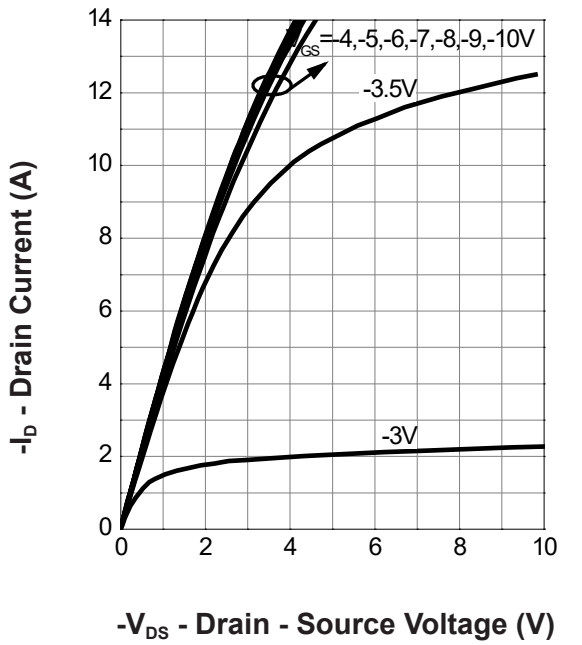
Safe Operation Area



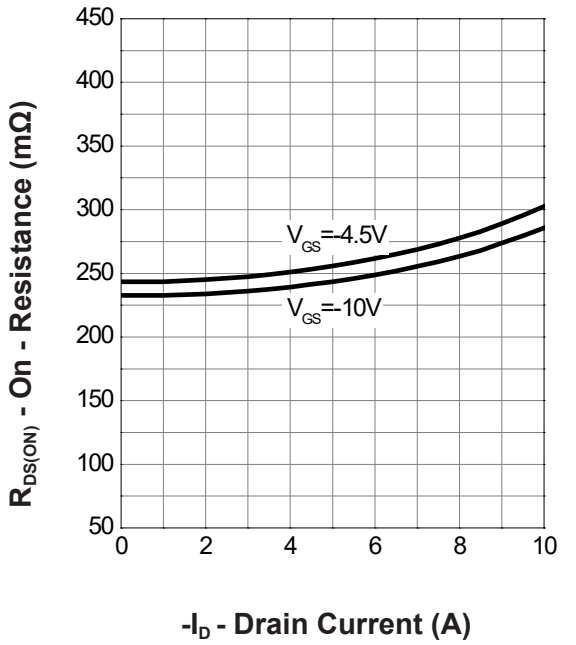
Thermal Transient Impedance



Output Characteristics



Drain-Source On Resistance



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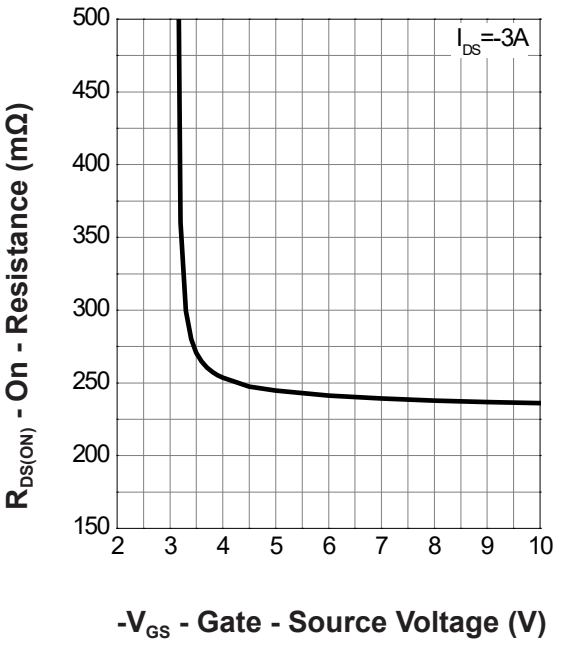
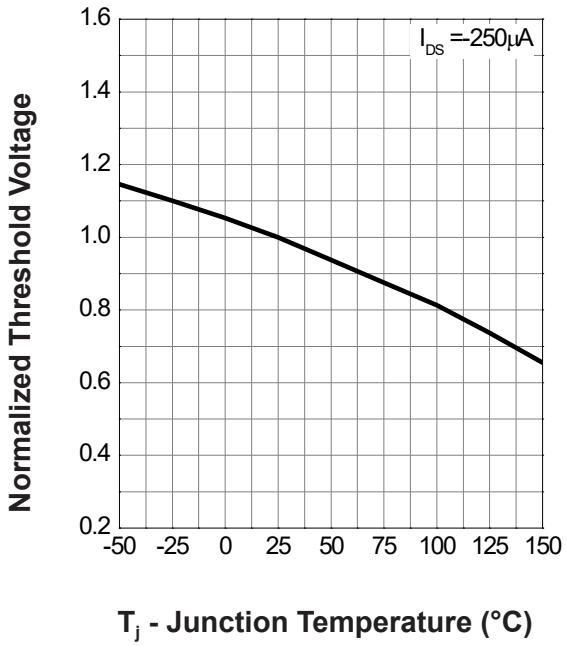
P Channel Typical Operating Characteristics(Cont.)

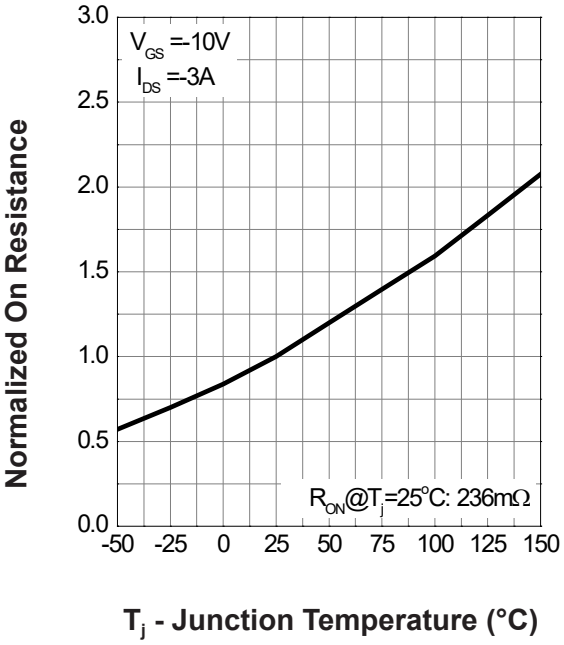
Gate-Source On Resistance



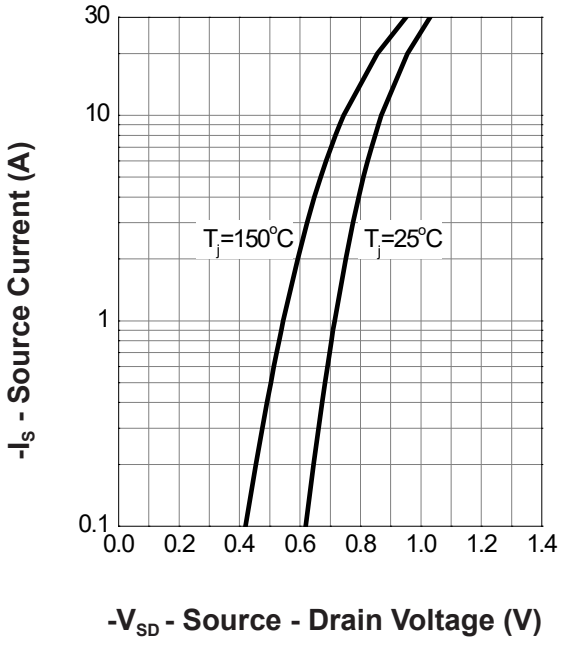
Gate Threshold Voltage



Drain-Source On Resistance



Source-Drain Diode Forward



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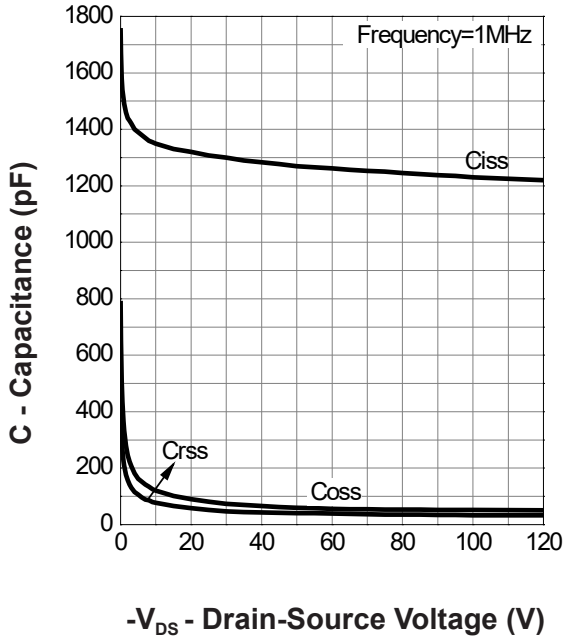
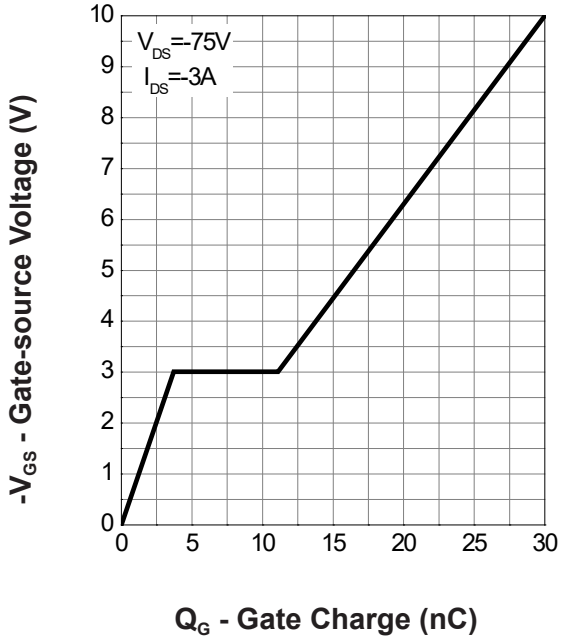
P Channel Typical Operating Characteristics(Cont.)

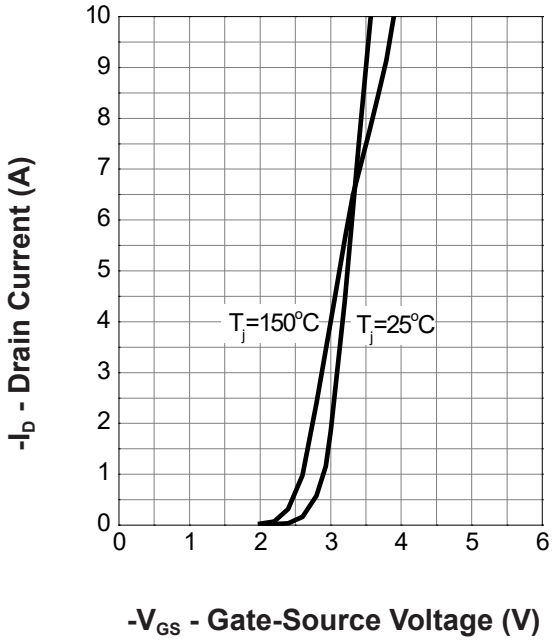
Capacitance



Gate Charge



Transfer Characteristics



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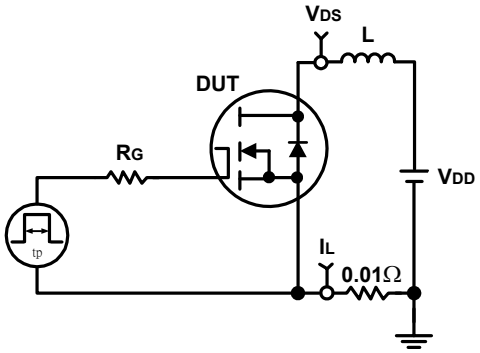
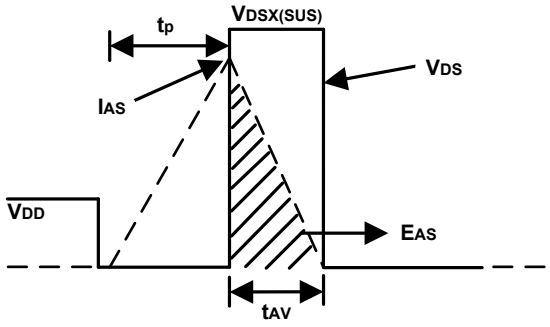
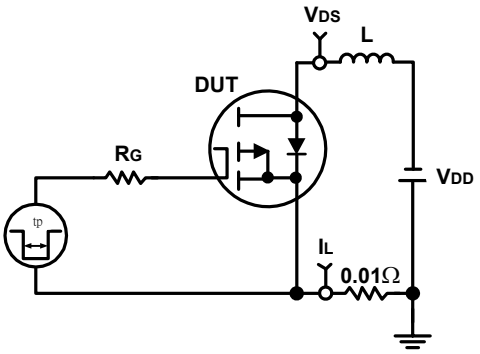
Avalanche Test Circuit and Waveforms

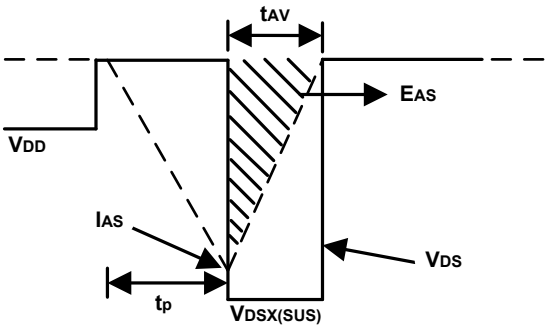
N Channel





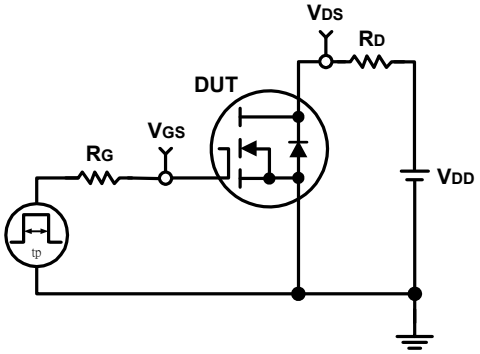
P Channel

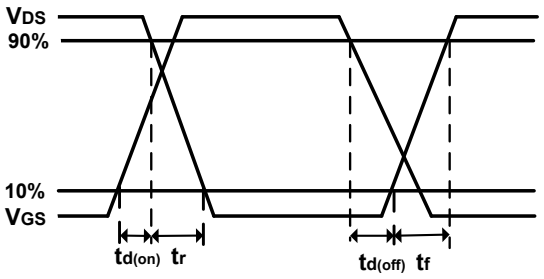




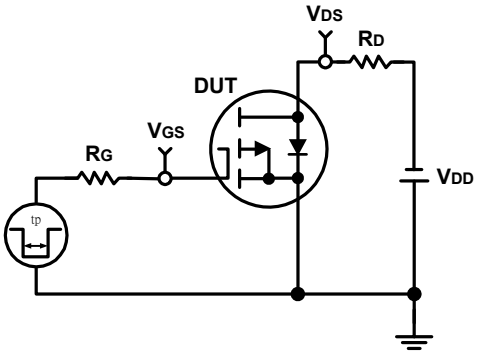
Switching Time Test Circuit and Waveforms

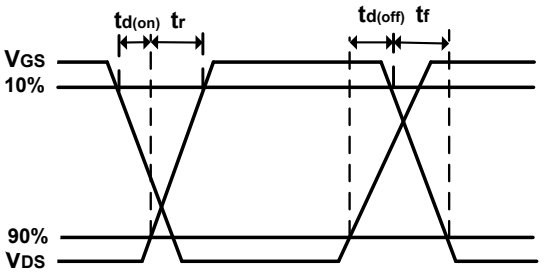
N Channel





P Channel





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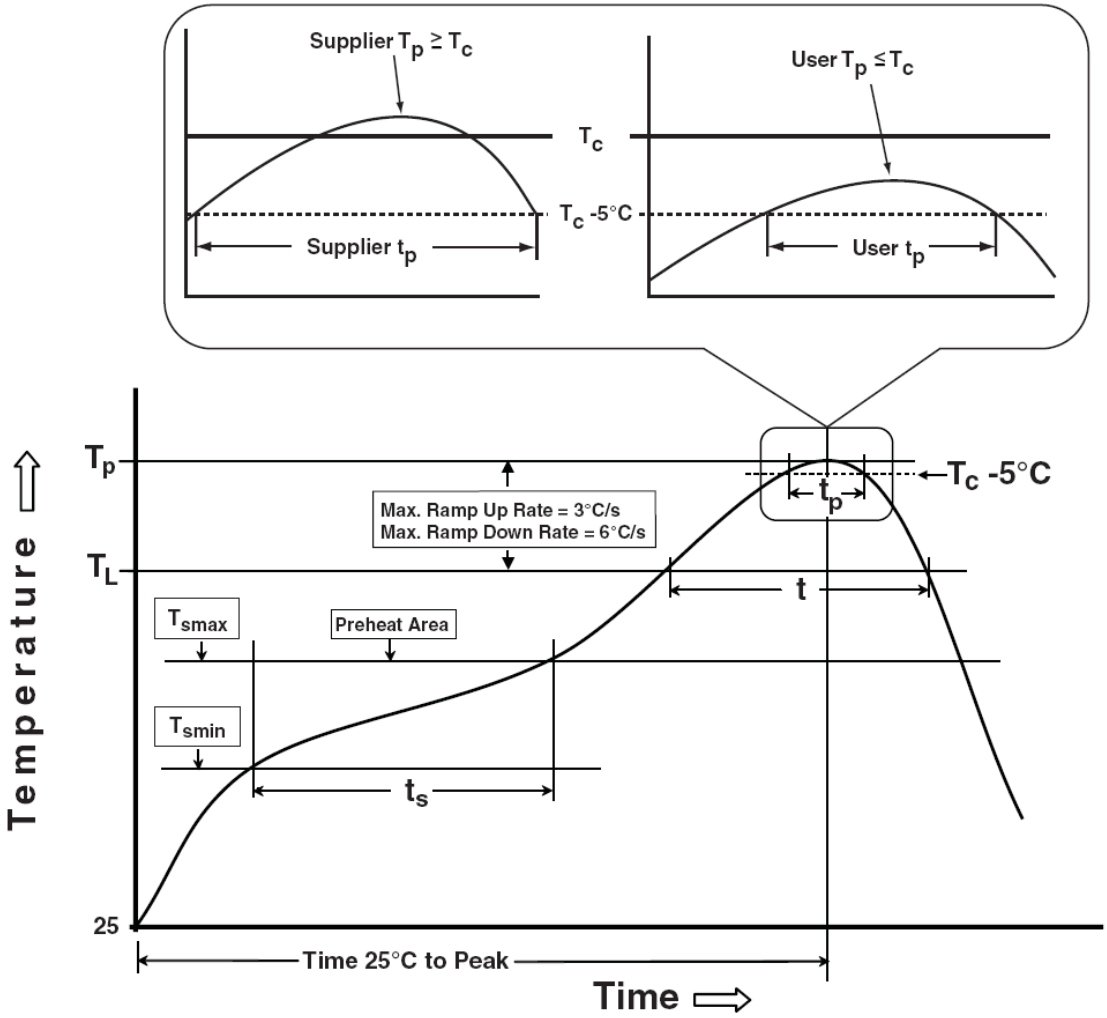
Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (T_{smin}) Temperature max (T_{smax}) Time (T_{smin} to T_{smax}) (t_s)	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds
Average ramp-up rate (T_{smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_P)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm^3 <350	Volume mm^3 ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm^3 <350	Volume mm^3 350-2000	Volume mm^3 >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ Tjmax
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ Tjmax
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

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